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(54) Title: DEVELOPABLE BOTTOM ANTIREFLECTIVE COATING COMPOSITIONS ESPECIALLY SUITABLE FOR ION IMPLANT APPLICATIONS AND METHOD OF FORMING A PATTERN USING IT

(57) Abstract: Compositions characterized by the presence of an aqueous base-soluble polymer having aromatic moieties and aliphatic alcohol moieties have been found which are especially useful as developable bottom antireflective coatings in 193nm lithographic processes. The compositions enable improved lithographic processes which are especially useful in the context of subsequent ion implantation or other similar processes where avoidance of aggressive antireflective coating removal techniques is desired.

DEVELOPABLE BOTTOM ANTIREFLECTIVE COATING COMPOSITIONS ESPECIALLY SUITABLE FOR ION IMPLANT APPLICATIONS AND METHOD OF FORMING A PATTERN USING IT

Background of the Invention

In the microelectronics industry as well as in other industries involving construction of microscopic structures (e.g. micromachines, magnetoresistive heads, etc.), there is a continued desire to reduce the size of structural features. In the microelectronics industry, the desire is to reduce the size of microelectronic devices and/or to provide greater amount of circuitry for a given chip size.

Effective lithographic techniques are essential to achieving reduction of feature sizes. Lithography impacts the manufacture of microscopic structures not only in terms of directly imaging patterns on the desired substrate, but also in terms of making masks typically used in such imaging. Typical lithographic processes involve formation of a patterned resist layer by patternwise exposing the radiation-sensitive resist to an imaging radiation. The image is subsequently developed by contacting the exposed resist layer with a material (typically an aqueous alkaline developer) to selectively remove portions of the resist layer to reveal the desired pattern. The pattern is subsequently transferred to an underlying material by etching the material in openings of the patterned resist layer or by ion implantation into the substrate at the spaces in the pattern corresponding to the removed portions. After the transfer is complete, the remaining resist layer is then typically removed.

For many lithographic imaging processes, the resolution of the resist image may be limited by anomalous effects associated with refractive index mismatch and undesired reflections of imaging radiation. High reflectivity from the substrate has become increasingly detrimental to the lithographic performance of photoresists for high NA and short UV wavelength (248nm and 193nm) exposures leading to undesirably high critical dimension (CD) variation on the wafer. This problem is even more pronounced in implant levels owing to the existence of topography (post gate level) and various reflective substrates (such as Si and SiO₂ in pregate levels).

Top antireflective coatings (TARC) have been used earlier, but their reflectivity control is not as good as bottom antireflective coatings (BARC).

Using conventional BARC requires an etch step (e.g., reactive ion etching) to remove the BARC. There is a concern that such etch processes could damage the substrate. Thus, the use of conventional BARC in the lithography step is not desirable for many applications including implant levels.

Developable BARC (DBARC) has been proposed to solve the damage issues associated with conventional BARC removal.

US Patent 6,844,131 describes a positive-working photoimageable bottom antireflective coating. This patent teaches the use of a polymer containing an acid labile group in combination with an absorbing chromophore. US Published Patent Application 20070243484 discloses a wet developable bottom antireflective coating composition and method for use thereof. This application teaches the use of a polymer containing no acid labile group. Both patent publications require the casting solvents for their DBARCs be different from the resist solvents. In most cases, these DBARC compositions require ketones and lactones. Ketones and lactones are usually either not safe enough or not good for spin-coating (the method commonly used to form layers of photoresist materials and BARCs on semiconductor wafers).

Therefore, there is a need for improved DBARC compositions that are especially suitable for use in 193nm lithographic processes to be followed by ion implantation which DBARCs use solvents that are more compatible with conventional photoresist processing and application techniques (e.g., propylene glycol methyl ether acetate or PGMEA).

Summary of the Invention

The invention encompasses developable bottom antireflective coating (DBARC) compositions comprising a polymer containing pendant aromatic moieties and pendant aliphatic alcohol-containing moieties. These DBARC compositions are characterized by the ability to apply them to substrates using conventional spin-coating and conventional solvents commonly used for casting resist materials. The compositions are further characterized by their ability, upon adequate baking (e.g., above about 150°C), to undergo little or no significant intermixing with the subsequently applied resist layer. Additionally, the DBARC compositions of the invention provide good reflectivity control (e.g., k value >0.15), good adhesion to substrate, upon adequate baking, and good dissolution properties in developer for the resist. The invention also encompasses methods of using such lithographic structures to pattern underlying material layers on a substrate.

In one aspect, the invention encompasses a developable bottom antireflective coating composition comprising:

- (a) a polymer containing a backbone component, a pendant aromatic moiety and a pendant aliphatic alcohol moiety, wherein the polymer becomes substantially insoluble in a resist casting solvent if subsequently baked at a temperature greater than about 150°C, and
- (b) a solvent for the unbaked polymer.

The polymer of the invention may contain pendant acid labile groups. The polymer preferably has an ethylenic backbone. The DBARC composition may further contain a radiation-sensitive acid generator. The DBARC composition itself may be photoimageable or not.

In another aspect, the invention encompasses method of forming a patterned material feature on a substrate, the method comprising:

- (c) providing a material surface on a substrate,
- (d) forming a bottom antireflective coating over the material surface, the bottom antireflective coating of the invention,

- (e) baking said antireflective coating layer to render it substantially insoluble in casting solvent for a subsequent resist layer,
- (f) forming a resist layer over the bottom antireflective coating,
- (g) patternwise exposing the resist layer to radiation thereby creating a pattern of radiation-exposed regions in the resist layer,
- (h) selectively removing portions of the resist layer and antireflective coating to expose portions of the material surface by selective dissolution in an aqueous alkaline developer, and
- (i) etching or ion implanting the exposed portions of the material, thereby forming the patterned material feature.

Step (g) preferably consists of ion implanting in the exposed portions. The imaging radiation is preferably 193nm radiation.

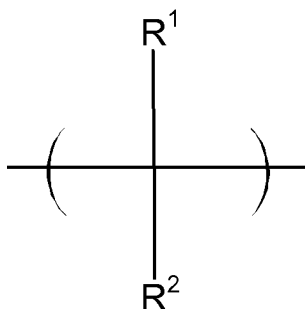
These and other aspects of the invention are discussed in further detail below.

Detailed Description of the Invention

The invention encompasses developable bottom antireflective coating (DBARC) compositions comprising a polymer containing pendant aromatic moieties and pendant aliphatic alcohol-containing moieties. These DBARC compositions are characterized by the ability to apply them to substrates using conventional spin-coating and conventional solvents commonly used for casting resist materials. The compositions are further characterized by their ability, upon adequate baking (e.g., above about 150°C), to undergo little or no significant intermixing with the subsequently applied resist layer. Additionally, the DBARC compositions of the invention provide good reflectivity control (e.g., k value >0.15), good adhesion to substrate, upon adequate baking, and good dissolution properties in developer for the resist. The invention also encompasses methods of using such lithographic structures to pattern underlying material layers on a substrate.

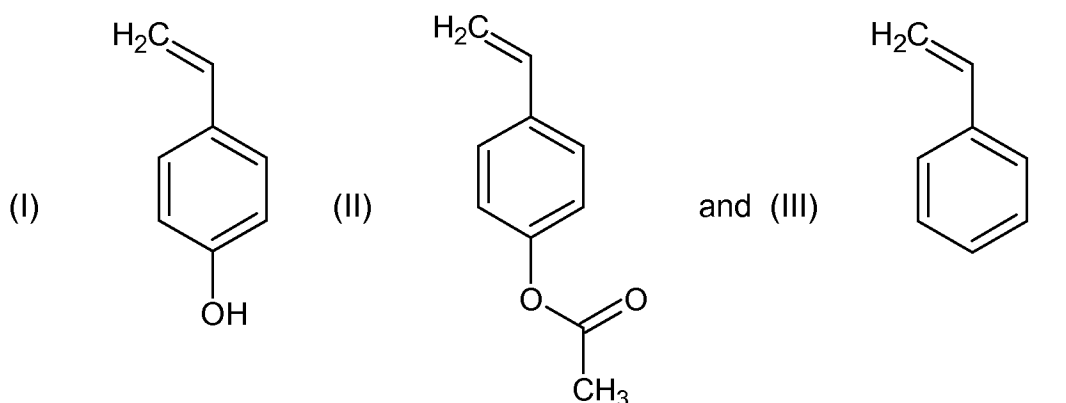
The polymer of the DBARC preferably has an ethylenic backbone. More preferably, the polymer contains vinyl, acrylate and/or methacrylate repeating units.

The polymer preferably contains a first repeating unit having the structure:

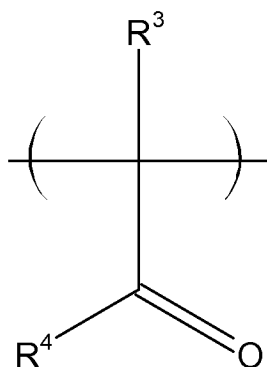


where R^1 is selected from H, F, Br, CF_3 , CN and CH_3 and R^2 includes an aromatic moiety. The aromatic moieties are preferably independently selected from the group consisting of substituted or unsubstituted aromatic moieties or combinations thereof. More preferably, aromatic moieties are selected from the group consisting of benzene, naphthalene, anthracene, phenanthrene, pyrene, coronene and combinations thereof. The polymer preferably contains about 10 to 80 mole % of repeating units having aromatic moieties, more preferably about 15-70 mole %, most preferably about 20-65 mole %.

Examples of specific first repeating units are derived from one of the following structures:

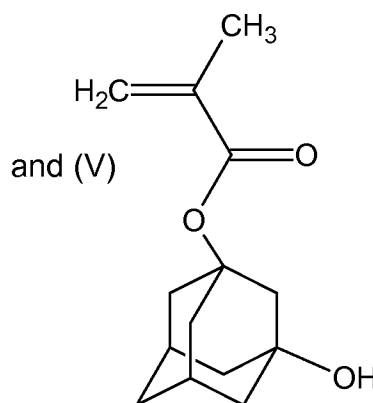
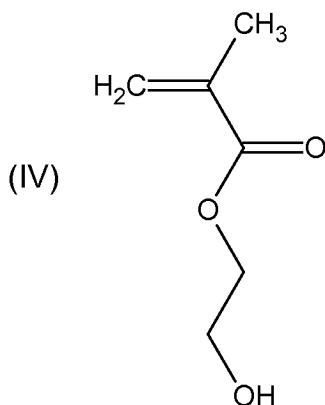


The polymer preferably contains a second repeating unit having the structure:



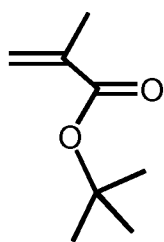
where R^3 is selected from H, F, Br, CF_3 , CN and CH_3 , R^4 includes an aliphatic alcohol moiety. The aliphatic alcohol moieties are preferably independently selected from the group consisting of linear, branched, and cycloaliphatic alcohols and combinations thereof. More preferably, the aliphatic alcohol moieties are selected from hydroxyadamantyl moieties, hydroxycyclohexyl, hydroxynorbornyl and hydroxyethyl moieties. The polymer preferably contains about 10 to 80 mole % of repeating units having aliphatic alcohol moieties, more preferably about 20-70 mole %, most preferably about 25-65 mole %.

Examples of specific second repeating units are derived from one of the following structures:

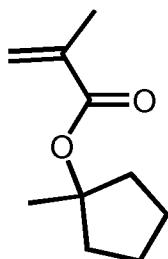


The invention also encompasses photoimageable DBARC compositions where the polymer preferably further includes third repeating units derived from a monomer which includes acid-labile pendant moieties, such as tertiary alkyl carbonates,

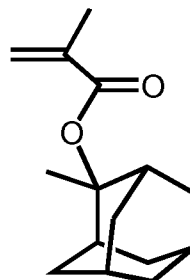
tertiary alkyl esters, tertiary alkyl ethers, acetals, and ketals. Some examples of such a monomer including a tertiary alkyl ester are shown below:



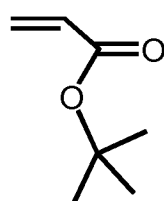
(VI)



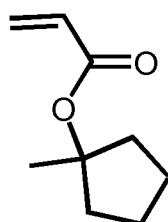
(VII)



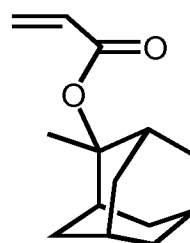
(VIII)



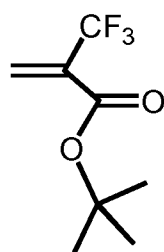
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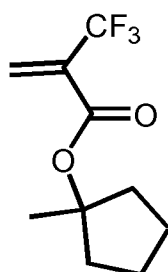
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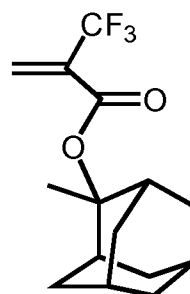
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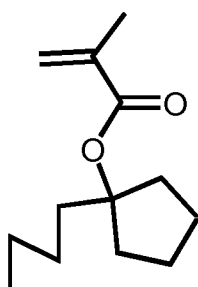
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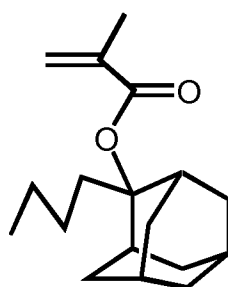
(XIII)



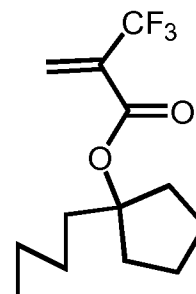
(XIV)



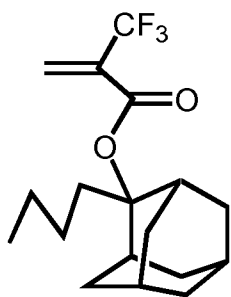
(XV)



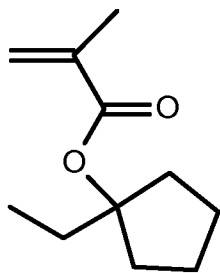
(XVI)



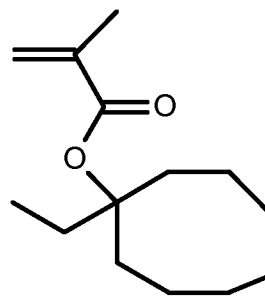
(XVII)



(XVIII),



(XIX),



(XX)

and

(XXI)

The DBARC compositions of the invention are not limited to any specific form of the third repeating unit. The DBARC polymer preferably includes about 10 - 65 mole % of the third repeating unit, more preferably about 15 - 50 mole %.

Some example DBARC polymers of the invention are described in the table below where the numbers indicate mole percent of repeating unit:

Sample name	Aromatic repeating unit	Acid labile repeating unit	Aliphatic alcohol repeating unit
WS-1	45 (HS)	40 (MAdMA)	15 (HAdMA)
WS-2	45 (HS)	40 (ECpMA)	15 (HAdMA)
WS-3	40 (HS)	35 (ECpMA)	25 (HAdMA)
WS-4	50 (HS)	25 (ECpMA)	25 (HAdMA)
WS-5	50 (AcOSt)	25 (ECpMA)	25 (HAdMA)
WS-6	40 (HS)	25 (ECpMA)	35 (HAdMA)
WS-7	50 (HS)	25 (ECpMA)	25 (HAdMA)
WS-8	30 (HS)	30 (ECpMA)	40 (HAdMA)
WS-9	25 (HS)	30 (ECpMA)	45 (HAdMA)
WS-10	30 (HS)	20 (ECpMA)	50 (HAdMA)
WS-11	30 (HS)	25 (EAdMA)	45 (HAdMA)
WS-12	30 (ST)	35 (ECpMA)	35 (HAdMA)
WS-13	30 (ST)	35 (EAdMA)	35 (HAdMA)
WS-14	30 (ST)	30 (ECpMA)	40 (HEMA)
W-15	30 (HS)	25 (MAdMA)	45 (HAdMA)
WS-16	30 (HS)	10 (MAdMA) 15 (ECpMA)	45 (HAdMA)
WS-17	30 (HS)	25 (TBA)	45 (HAdMA)
WS-18	30 (HS)	25 (MCpMA)	45 (HAdMA)
S-1	85 (HS)		15 (HAdMA)

HS = 4-hydroxystyrene (structure I)

AcOSt = 4-Acetoxy styrene (structure II)

ST = styrene (structure III)

MAdMA = MethylAdamantylMethacrylate (structure VIII)

EAdMA = EthylAdamantylMethacrylate (structure XXI)

ECpMA = EthylCyclopentylMethacrylate (structure XIX)

MCpMA = MethylCyclopentylMethacrylate (structure VII)

TBA = tert-ButylAcrylate (structure VI)

HAdMA = HydroxyAdamantylMethacrylate (structure V)

HEMA = HydroxyEthylMethacrylate (structure IV)

The DBARC compositions of the invention preferably have an extinction coefficient k of about >0.15 with respect to a radiation wavelength of 193nm.

The DBARC polymers of the invention preferably have a weight average molecular weight of at least about 1000, more preferably a weight average molecular weight of about 1500-50000, most preferably about 8000 to 15000. The polymers of the invention may be made by conventional polymerization techniques using commercially available and/or easily synthesized monomers. If desired, blends of different polymers of the invention may be used.

The invention also encompasses photoimageable DBARC compositions where the composition preferably contains a radiation sensitive acid generator.

The radiation sensitive acid generators, also known as photoacid generators, used in the photoresist composition of the invention are compounds that generate an acid upon exposure to radiation. Any suitable photoacid generating agent may be used, so long as the resulting DBARC composition dissolves sufficiently in the casting solvent and the resulting solution thereof forms a suitably uniform film by a film-forming process, such as spin coating or the like. Some examples of classes of photoacid generators that may be employed in the DBARC compositions of the invention are: onium salts, succinimide derivatives, diazo compounds, nitrobenzyl compounds, and the like. The photoacid generators may be used singly or in a mixture of two or more.

Some preferred photoacid generators are onium salts, such as an iodonium salt or a sulfonium salt, and/or a succinimide derivative. More preferred photoacid generators include 4-(1-butoxynaphthyl) tetrahydrothiophenium perfluorobutanesulfonate, triphenyl sulfonium perfluorobutanesulfonate, t-butylphenyl diphenyl sulfonium perfluorobutanesulfonate, 4-(1-butoxynaphthyl) tetrahydrothiophenium perfluorooctanesulfonate, triphenyl sulfonium perfluorooctanesulfonate, t-butylphenyl diphenyl sulfonium perfluorooctanesulfonate, di(t-butylphenyl) iodonium perfluorobutane sulfonate, di(t-butylphenyl) iodonium perfluorohexane sulfonate, di(t-butylphenyl) iodonium perfluoroethylcyclohexane sulfonate, di(t-butylphenyl)iodonium camphorsulfonate, and perfluorobutylsulfonyloxybicyclo[2.2.1]-hept-5-ene-2,3-dicarboximide.

The compositions of the invention may further comprise at least one solvent. Suitable solvents include, but are not limited to: PGMEA, ethyl lactate, ethyl 3-ethoxypropionate, cyclohexanone, 1-butanol, methanol, ethanol, 1-propanol, ethylene glycol, 1,2-butanediol, 1,3-butanediol, 1,4-butanediol, 1,2-propanediol, 1-pentanol, 2-pentanol, 3-pentanol, 1-hexanol, 2-hexanol, 3-hexanol, 1-heptanol, 2-heptanol, 3-heptanol, 4-heptanol, 2-methyl-1-pentanol, 2-methyl-2-pentanol, 2-methyl-3-pentanol, 3-methyl-1-pentanol, 3-methyl-2-pentanol, 3-methyl-3-pentanol, 4-methyl-1-pentanol, 4-methyl-2-pentanol, 2,4-dimethyl-3-pentanol, 3-ethyl-2-pentanol, 1-methylcyclopentanol, 2-methyl-1-hexanol, 2-methyl-2-hexanol, 2-methyl-3-hexanol, 3-methyl-3-hexanol, 4-methyl-3-hexanol, 5-methyl-1-hexanol, 5-methyl-2-hexanol, 5-methyl-3-hexanol, 4-methylcyclohexanol, 1,3-propanediol, octanol, and decane. The composition may further comprise small portion of second or third solvent to form a mixed solvent. Suitable second or third solvents include, but not limited to: γ -butyrolactone, anisole, propylene carbonate, sulfolane, dimethyl succinate, and dimethyl adipate. Preferably, the solvent is one used for casting of resist formulations. The amount of solvent in the composition for application to a substrate is preferably sufficient to achieve a solids content of about 0.5-5 wt.%. The compositions may include surfactants, acid quenchers or other expedients known in the art.

The invention encompasses methods of forming a patterned material feature on a substrate, the method comprising:

- (j) providing a material surface on a substrate,
- (k) forming a bottom antireflective coating over the material surface, the bottom antireflective coating comprising
 - a polymer containing a backbone component, a pendant aromatic moiety and a pendant aliphatic alcohol moiety, wherein the polymer becomes substantially insoluble in a resist casting solvent if subsequently baked at a temperature greater than about 150°C, and
- (l) a solvent for the unbaked polymer,
- (m) baking the antireflective coating layer to render it substantially insoluble in casting solvent for a subsequent resist layer,

- (n) forming a resist layer over the bottom antireflective coating,
- (o) patternwise exposing the resist layer to radiation thereby creating a pattern of radiation-exposed regions in the resist layer,
- (p) selectively removing portions of the resist layer and antireflective coating to expose portions of the material surface by selective dissolution in an aqueous alkaline developer, and
- (q) etching or ion implanting the exposed portions of the material, thereby forming the patterned material feature.

The material surface of the semiconductor substrate may be a metal conductor layer, a ceramic insulator layer, a semiconductor layer or other material depending on the stage of the manufacture process and the desired material set for the end product. The compositions of the invention are especially useful for lithographic processes used in the manufacture of integrated circuits on semiconductor substrates. The compositions of the invention in lithographic processes to create patterned material layer structures such as metal wiring lines, holes for contacts or vias, insulation sections (e.g., damascene trenches or shallow trench isolation), trenches for capacitor structures, ion implanted Si structures for transistors, etc. as might be used in integrated circuit devices.

The DBARC compositions of the invention preferably will substantially reduce the substrate reflectivity with respect to 193nm radiation. The DBARC composition of the invention is preferably applied directly over the material surface by spin-coating. The DBARC is then baked for a time and temperature sufficient to remove any solvent in the DBARC composition and to render the DBARC composition substantially insoluble in the solvent used to apply the subsequent resist layer. The baking temperature is preferably about 110°C or higher, more preferably about 150°C to 250°C. The bake time is preferably about 30 seconds to 5 minutes, more preferably about 1 to 2 minutes. For DBARCs containing acid labile groups, overbaking would result in a substantial deprotection of the polymers and would then become largely or completely dissolved away in the develop process to form the undesired undercut profiles or collapsed images. Overbaking may in some

instances create insoluble component such as to form residues after develop process. Preferably, overbaking such as would hinder solubility of the DBARC in aqueous base developer is avoided.

The resist is preferably imageable with 193nm ultraviolet radiation. Examples of suitable resist materials are described in US Published Patent Application Nos. 20050153232A1 and 20040063024A1 and US Patents 6902874, 6730452, 6627391, 6635401 and 6756180 the disclosures of which are incorporated herein by reference. Typically, the solvent-containing resist composition is applied using spin coating or other technique. The substrate with the resist coating is then preferably heated (pre-exposure baked) to remove the solvent and improve the coherence of the resist layer. The pre-exposure bake step is preferably conducted for about 10 seconds to 15 minutes, more preferably about 15 seconds to one minute. The pre-exposure bake temperature may vary depending on the glass transition temperature of the resist.

If desired, a top antireflective coating may be applied to the substrate after formation of the resist layer according to conventional techniques.

The resist layer is then patternwise-exposed to the desired radiation (e.g. 193 nm ultraviolet radiation). The patternwise exposure is conducted through a mask which is placed over the resist layer. For 193 nm UV radiation, the total exposure energy is preferably about 100 millijoules/cm² or less, more preferably about 50 millijoules/cm² or less (e.g. 15-30 millijoules/cm²).

After the desired patternwise exposure, the resist layer is typically baked to further complete the acid-catalyzed reaction and to enhance the contrast of the exposed pattern. The post-exposure bake is preferably conducted at about 60-175°C, more preferably about 90-160°C. The post-exposure bake is preferably conducted for about 30 seconds to 5 minutes.

After post-exposure bake, if any, the resist structure with the desired pattern is obtained (developed) by contacting the resist layer with an aqueous alkaline developer solution which selectively dissolves the areas of the resist which were exposed to radiation in the case of a positive resist (or the unexposed areas in the case of a negative resist). The DBARC in the area of the dissolved resist is also removed by dissolution in the aqueous base developer solution. Preferred aqueous base developer solutions are aqueous solutions of tetramethyl ammonium hydroxide. The resulting lithographic structure on the substrate is then typically dried to remove any remaining developer.

The pattern from the resist structure may then be transferred to the exposed portions of underlying material of the substrate by etching with a suitable etchant using techniques known in the art (e.g., reactive ion etching or wet etching) or by ion implantation in the exposed portions. The invention is especially useful where the pattern transfer is performed by ion implantation (e.g., dopant implantation to form source/drain features in semiconductor materials). Once the desired pattern transfer has taken place, any remaining resist may be removed using conventional stripping techniques.

Examples of general lithographic processes where the composition of the invention may be useful are disclosed in US Patents 4,855,017; 5,362,663; 5,429,710; 5,562,801; 5,618,751; 5,744,376; 5,801,094; 5,821,469 and 5,948,570, the disclosures of which patents are incorporated herein by reference. Other examples of pattern transfer processes are described in Chapters 12 and 13 of "Semiconductor Lithography, Principles, Practices, and Materials" by Wayne Moreau, Plenum Press, (1988), the disclosure of which is incorporated herein by reference. It should be understood that the invention is not limited to any specific lithography technique or device structure.

The invention is further described by the examples below. The invention is not limited to the specific details of the examples.

EXAMPLE 1

Synthesis of terpolymers of 4-hydroxystyrene, 1-ethylcyclopentyl methacrylate, and 3-hydroxy-1-adamantyl methacrylate (HS/ECpMA/HAdMA(30/20/50)) (WS-10)

To a round bottom flask equipped with condenser, thermometer, an argon (Ar) inlet, and a magnetic stirrer bar, the following were added: 4-acetoxystyrene monomer (2.43 grams (g), 0.015 mole), 1-ethylcyclopentyl methacrylate monomer (1.82 g, 0.01 mole), 3-hydroxy-1-adamantyl methacrylate monomer (5.91g, 0.025 mole), 2,2'-azobis(2-methylpropionitrile) (AIBN)(0.41 g, 5 % of total moles of monomers), and approximately 40 g of tetrahydrofuran (THF). The reaction mixture was stirred at room temperature and bubbled with Ar flow for 45 minutes before it was heated. The reaction was carried out overnight at 72 °C under an inert Ar atmosphere. The reaction solution was then cooled to room temperature and approximately 20 g of THF was blown away by a high flow of nitrogen bubbling into the flask. To the remaining reaction solution, 18 g of methanol and approximately 4 g (excess) of concentrated NH₄OH were added and the reaction was carried out at 65 °C overnight. The solution was then cooled to room temperature, and small portion of the reaction mixture was removed for C¹³ NMR test. The mixture was added in with equivalent of deuterated acetone for this test. After the confirmation of complete deprotection of acetoxy group (the disappearance of 121 ppm peak), the reaction solution was then added dropwise into a mixture of water (1000 ml) and glacial acetic acid (30ml). The precipitated polymer was separated, rinsed with water (2 x 300 ml) and dried in a vacuum oven at 65 °C for a short time. The polymer was re-dissolved in acetone and re-precipitated in a mixture of water (1000 ml) and glacial acetic acid (30 ml). The solid was filtered with a frit funnel, washed with water (2 x 300 ml) and dried in a vacuum oven at 65 °C for 24 hours.

EXAMPLE 2

Synthesis of terpolymers of 4-hydroxystyrene, t-butyl acrylate, and 3-hydroxy-1-adamantyl methacrylate (HS/TBA/HAdMA(30/25/45)) (WS-17)

To a round bottom flask equipped with condenser, thermometer, an argon (Ar) inlet, and a magnetic stirrer bar, the following were added: 4-acetoxystyrene monomer (2.43 grams (g), 0.015 mole), t-butyl acrylate monomer (1.6 g, 0.0125 mole), 3-hydroxy-1-adamantyl methacrylate monomer (5.319g, 0.0225 mole), 2,2'-azobis(2-methylpropionitrile) (AIBN)(0.328 g, 4 % of total moles of monomers), and approximately 40 g of tetrahydrofuran (THF). The reaction mixture was stirred at room temperature and bubbled with Ar flow for 45 minutes before it was heated. The reaction was carried out overnight at 72 °C under an inert Ar atmosphere. The rest of the synthetic procedures are the same as Example 1, except approximately 5g of concentrated NH₄OH was used in deprotecting the acetoxy groups from acetoxystyrene repeat units to form hydroxyl styrene repeat units of the terpolymer.

EXAMPLE 3

Patterning of HS/ECpMA/HAdMA(30/20/50) polymer

Formulation was prepared by dissolving 100mg of polymer prepared in EXAMPLE 1 and 5 mg of TPS PFBuS in 4-methyl-2-pentanol. It was then filtered through 0.2 µm PTFE filter and spincoated onto a clean silicon wafer at about 1500 RPM. The wafer was then baked at 180 °C for 60 sec. Subsequently the wafer was coated with a ArF photoresist and imaged using binary mask in a ArF stepper. The wafer was baked at 100 °C and developed in a standard 0.26N developer. The X-SEM of printed pattern for 135 nm lines/spaces showed improved sidewall profile compared to images created without use of the DBARC of the invention.

EXAMPLE 4

Patterning of HS/TBA/HAdMA(30/25/45) polymer

Formulation was prepared by dissolving 100mg of polymer prepared in EXAMPLE 2 and 5 mg of TPS PFBuS in 4-methyl-2-pentanol. It was then filtered through 0.2 µm PTFE filter and spin-coated onto a clean silicon wafer at about 1500 RPM. The wafer was then baked at 180 °C for 60 sec. Subsequently the wafer was coated with a ArF photoresist and imaged using binary mask in a ArF stepper. The wafer was

baked at 110 °C and developed in a standard 0.26N developer. The X-SEM of printed pattern for 135 nm lines/spaces showed improved sidewall profile compared to images created without use of the DBARC of the invention.

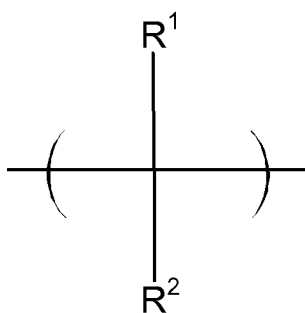
EXAMPLE 5

Aqueous base test of baked HS-HAdMA(85/15) (S1) copolymer

A HS-HAdMA(85/15) Copolymer was prepared in the manner described in Example 1. The copolymer was spin coated onto a substrate using a casting solvent of 2% GBL and 98% PGMEA. The sample was then baked at 185 °C for 1 minute. The resulting film was then contacted with an aqueous alkaline developer for 60 seconds which resulted in complete dissolution of the baked DBARC.

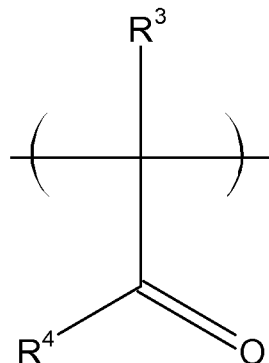
CLAIMS

1. A developable bottom antireflective coating composition comprising:
 - (a) a polymer containing a backbone component, a pendant aromatic moiety and a pendant aliphatic alcohol moiety, wherein said polymer becomes substantially insoluble in a resist casting solvent if subsequently baked at a temperature greater than about 150°C, and
 - (b) a solvent for said unbaked polymer.
2. The composition of claim 1 said composition wherein said polymer further comprises a pendant acid labile moiety.
3. The composition of claim 1 further comprising (c) a radiation-sensitive acid generator.
4. The composition of claim 1 wherein said backbone component is an ethylenic backbone.
5. The composition of claim 1 wherein said polymer comprises a first repeating unit having the structure:



wherein R¹ is selected from H, F, Br, CF₃, CN and CH₃ and R² includes an aromatic moiety.

6. The composition of claim 5 wherein said polymer comprises a second repeating unit having the structure:



- wherein R³ is selected from H, F, Br, CF₃, CN and CH₃, R⁴ includes an aliphatic alcohol moiety.
7. The composition of claim 6 wherein said polymer comprises a third repeating unit, said third repeating unit having an acid labile moiety.
8. The composition of claim 5 wherein said aromatic moieties are selected from the group consisting of benzene, naphthalene, anthracene, phenanthrene, pyrene, coronene and combinations thereof.
9. The composition of claim 6 wherein said aliphatic alcohol moieties are selected from the group consisting of linear, branched, and cycloaliphatic alcohols and combinations thereof.
10. The composition of claim 9 wherein said polymer comprises cycloaliphatic alcohol moieties.
11. The composition of claim 10 wherein said cycloaliphatic alcohol moieties are hydroxyadamantyl moieties.
12. The composition of claim 6 wherein said polymer consists essentially of said repeating units.

13. The composition of claim 7 wherein said polymer consists essentially of said repeating units.
14. The composition of claim 1 wherein said solvent for said unbaked polymer is selected from the group consisting of propylene glycol methyl ether acetate, 4-methyl-2-pentanol, cyclohexanone, ethyl lactate, ethyl 3-ethoxypropionate.
15. The composition of claim 7 wherein said polymer has 15 -70 mole % of said first repeating unit, 20 - 70 mole % of said second repeating unit, and 10 - 65 mole % of said third repeating unit.
16. The composition of claim 1 wherein said polymer has a weight average molecular weight of about 1500-50000.
17. A method of forming a patterned material feature on a substrate, said method comprising:
 - (a) providing a material surface on a substrate,
 - (b) forming a bottom antireflective coating over said material surface, said bottom antireflective coating comprising
 - (i) a polymer containing a backbone component, a pendant aromatic moiety and a pendant aliphatic alcohol moiety, wherein said polymer becomes substantially insoluble in a resist casting solvent if subsequently baked at a temperature greater than about 150°C, and
 - (ii) a solvent for said unbaked polymer,
 - (c) baking said antireflective coating layer to render it substantially insoluble in casting solvent for a subsequent resist layer,
 - (d) forming a resist layer over said bottom antireflective coating,
 - (e) patternwise exposing said resist layer to radiation thereby creating a pattern of radiation-exposed regions in said resist layer,

- (f) selectively removing portions of said resist layer and antireflective coating to expose portions of said material surface by selective dissolution in an aqueous alkaline developer, and
 - (g) etching or ion implanting said exposed portions of said material, thereby forming said patterned material feature.
18. The method of claim 17 wherein said antireflective coating further comprises (iii) a radiation-sensitive acid generator.
19. The method of claim 17 wherein said polymer further comprises a pendant acid labile moiety.
20. The method of claim 17 wherein said resist casting solvent is propylene glycol methyl ether acetate.
21. The method of claim 17 wherein ion implanting is performed instep (g).
22. The method of claim 17 wherein said radiation is ultraviolet radiation having a wavelength of about 193nm.

INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2010/050796

A. CLASSIFICATION OF SUBJECT MATTER
INV. G03F7/09 G03F7/039

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
G03F

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data, COMPENDEX

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	WO 2005/093513 A2 (AZ ELECTRONIC MATERIALS USA [US]) 6 October 2005 (2005-10-06)	1-9, 12-20,22
Y	Synthesis Example 5, formula (V); page 8, line 12 - page 12, line 25; claims 1-16; example 7	10-11
X	WO 2004/048458 A1 (DONGJIN SEMICHEM CO LTD [KR]; KIM JAE-HYUN [KR]; LEE CHUN-HYUK [KR]; Y) 10 June 2004 (2004-06-10)	1-9, 13-20,22
Y	page 8, line 8 - page 13, line 17; claims 1-10; examples 1-3	10-11,21
Y	US 2005/266354 A1 (LI WENJIE [US] ET AL LI WENJIE [US] ET AL) 1 December 2005 (2005-12-01)	10-11
	paragraphs [0011], [0022]; claim 1; example 3; compound XXI	
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Further documents are listed in the continuation of Box C.

See patent family annex.

* Special categories of cited documents :

- *A* document defining the general state of the art which is not considered to be of particular relevance
- *E* earlier document but published on or after the international filing date
- *L* document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)
- *O* document referring to an oral disclosure, use, exhibition or other means
- *P* document published prior to the international filing date but later than the priority date claimed

- *T* later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
- *X* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
- *Y* document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.
- *&* document member of the same patent family

Date of the actual completion of the international search

26 March 2010

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08/04/2010

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INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2010/050796

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	US 2008/206690 A1 (KENNEDY JOSEPH [US] ET AL) 28 August 2008 (2008-08-28) paragraph [0015] -----	21

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

PCT/EP2010/050796

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